

Session Title: [TA3] RF Power Amplifier

Session Date: December 4 (Thu.), 2025

Session Time: 13:20-15:00

Session Room: Room A (Halla A)

Session Chair(s): Padmanava Sen (Barkhausen Institut gGmbH, Germany)
Seungchan Lee (Chonnam National University, Korea)

[TA3-1] [Invited] 13:20-13:40

An Improved Noise Figure Measurement Technique for Differential Amplifiers

Bharatha Kumar Thangarasu, Shuai Li, Hongshi Yu, Wansi Ge, Xiaozheng Guo, Yuqing Liu, Sini Wu, Nagarajan Mahalingam, Fanyi Meng and Kaixue Ma (Tianjin University, China); Zhenghao Lu (Soochow University, China); Kiat Seng Yeo (Singapore University of Technology and Design, Singapore & Tianjin University, China)

[TA3-2] 13:40-14:00

6-18 GHz GaN High Power Amplifier MMIC for Multi-Function Radar Application

Moongyu Kim, Kyungdong Bae, Yoonjung Lee and Youngoo Yang (Sungkyunkwan University, Korea (South))

[TA3-3] 14:00-14:20

A Ka-Band Harmonic-Tuned GaN Doherty Power Amplifier

Moise Safari Mugisho, Christian Friesicke, Dirk Schwantuschke, Peter Brückner and Rüdiger Quay (Fraunhofer IAF, Germany)

[TA3-4] 14:20-14:40

Novel Inductively-Gated FET Diodes for Microwave Rectifiers

Taisei Shimada and Shinichi Tanaka (Shibaura Institute of Technology, Japan)

[TA3-5] 14:40-15:00

Asymmetric Doherty Power Amplifier Design Based on Load-Pull Driven Current Ratio Optimization for Accurate Load Modulation

Jisu Park and Minjae Ahn (Konkuk University, Korea (South)); Dongsu Kim and Yunsik Park (Korea Electronics Technology Institute, Korea (South)); Hyunchul Ku (Konkuk University, Korea (South))